

Supporting Information

Efficient stress-relaxation in InGaN/GaN light-emitting diodes using carbon nanotubes

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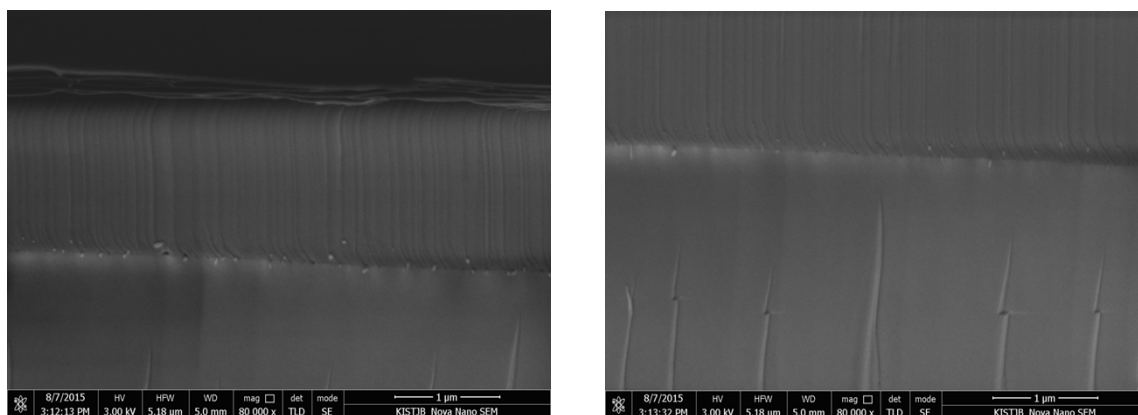


Figure S1. Cross-sectional FESEM images showing the interface of GaN/SWCNTs-coated sapphire.

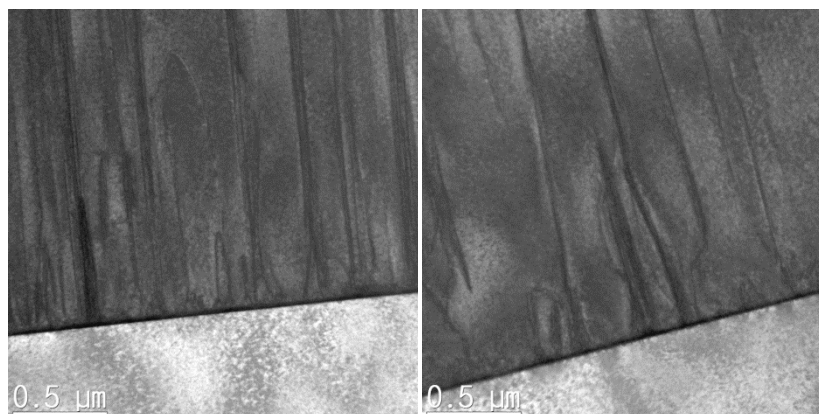


Figure S2. Cross-sectional HRTEM images of GaN at the very interface of (a) sapphire and (b) HD-SWCNTs/sapphire.

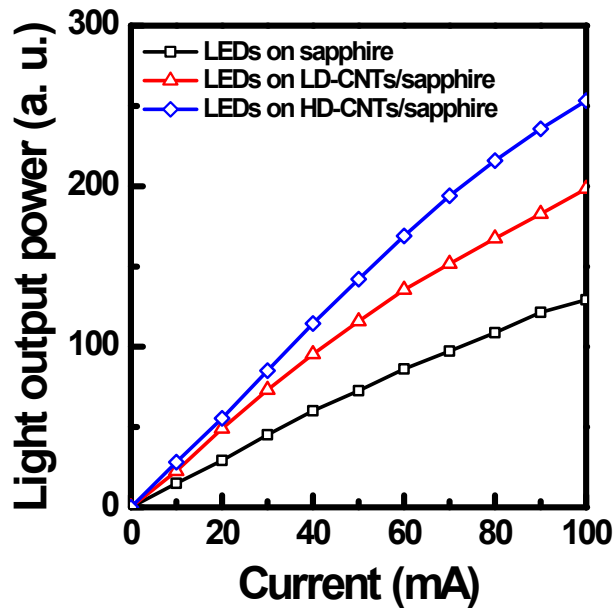


Figure S3. Light output power of the LEDs measured as a function of injection current. The measurements were performed at wafer scale on individual chips by keeping the distance of separation between the wafer and the photodetector constant for all the samples.